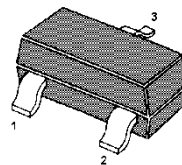


BC846...BC850

NPN Silicon Epitaxial Transistor

for switching and amplifier applications

As complementary types the PNP transistors BC856...BC860 is recommended.



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	BC846	V_{CBO}	80	V
	BC847, BC850	V_{CBO}	50	V
	BC848, BC849	V_{CBO}	30	V
Collector Emitter Voltage	BC846	V_{CEO}	65	V
	BC847, BC850	V_{CEO}	45	V
	BC848, BC849	V_{CEO}	30	V
Emitter Base Voltage	BC846, BC847	V_{EBO}	6	V
	BC848, BC849, BC850	V_{EBO}	5	V
Collector Current	I_C	100	mA	
Peak Collector Current	I_{CM}	200	mA	
Power Dissipation	P_{tot}	300	mW	
Junction Temperature	T_j	150	$^\circ\text{C}$	
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$	

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
ISO 9001 : 2008 Certificate No. 50114012
OHSAS 18001 : 2007 Certificate No. 05191508008
IECQ QC 080000 Certificate No. E241000744M2

Dated: 27/04/2016 Rev: 03

BC846...BC850

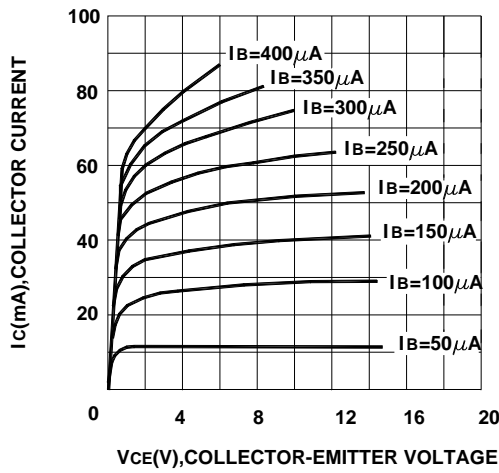
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$	Current Gain Group A	h_{FE}	110	-	220	-
	B	h_{FE}	200	-	450	-
	C	h_{FE}	420	-	800	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	15	nA	
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	BC846	$V_{(BR)CBO}$	80	-	-	V
	BC847, BC850	$V_{(BR)CBO}$	50	-	-	V
	BC848, BC849	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	BC846	$V_{(BR)CEO}$	65	-	-	V
	BC847, BC850	$V_{(BR)CEO}$	45	-	-	V
	BC848, BC849	$V_{(BR)CEO}$	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	BC846, BC847	$V_{(BR)EBO}$	6	-	-	V
	BC848, BC849, BC850	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ at $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	-	-	250	mV	
	V_{CEsat}	-	-	600	mV	
Base Emitter On Voltage at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	$V_{BE(on)}$	580	-	700	mV	
	$V_{BE(on)}$	-	-	720	mV	
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	300	-	MHz	
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	6	pF	
Input Capacitance at $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{ib}	-	9	-	pF	

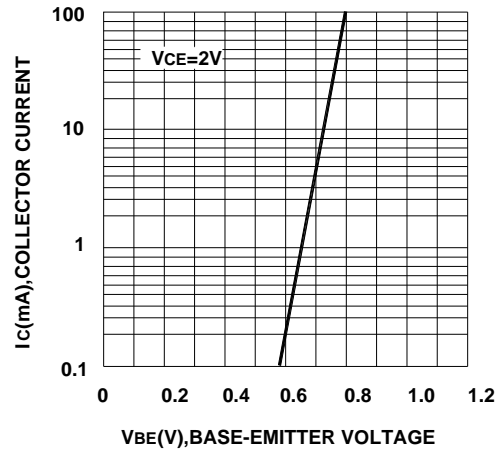
TOP DYNAMIC



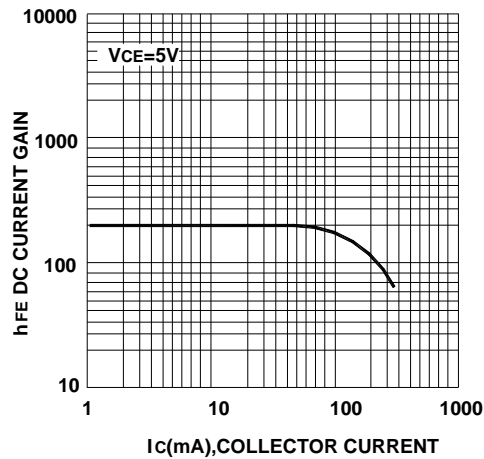
STATIC CHARACTERISTIC



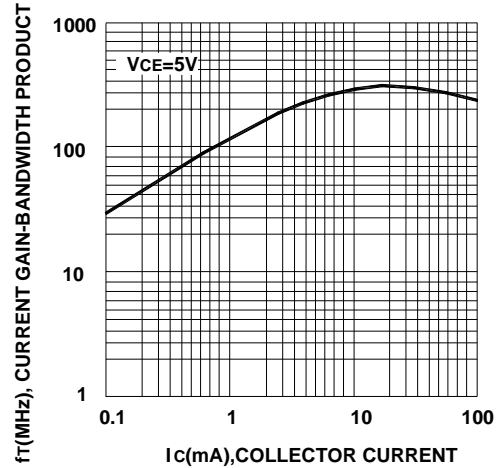
BASE-EMITTER ON VOLTAGE



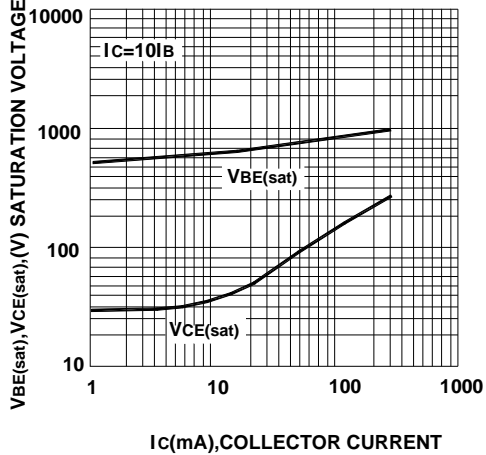
DC CURRENT GAIN



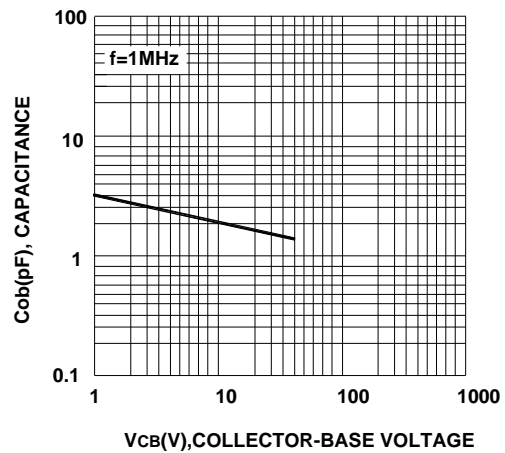
CURRENT GAIN BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



TOP DYNAMIC

